

Rihito Kuroda

List of Publications by Year in descending order

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| # | ARTICLE | IF | CITATIONS |
|----|---|-----|-----------|
| 1 | A Global-Shutter CMOS Image Sensor With Readout Speed of 1-Tpixel/s Burst and 780-Mpixel/s Continuous. IEEE Journal of Solid-State Circuits, 2013, 48, 329-338. | 5.4 | 86 |
| 2 | Atomically Flat Silicon Surface and Silicon/Insulator Interface Formation Technologies for (100) Surface Orientation Large-Diameter Wafers Introducing High Performance and Low-Noise Metalâ€“Insulatorâ€“Silicon FETs. IEEE Transactions on Electron Devices, 2009, 56, 291-298. | 3.0 | 59 |
| 3 | Revolutional Progress of Silicon Technologies Exhibiting Very High Speed Performance Over a 50-GHz Clock Rate. IEEE Transactions on Electron Devices, 2007, 54, 1471-1477. | 3.0 | 45 |
| 4 | Complementary Metalâ€“Oxideâ€“Silicon Field-Effect-Transistors Featuring Atomically Flat Gate Insulator Film/Silicon Interface. Japanese Journal of Applied Physics, 2009, 48, 04C048. | 1.5 | 28 |
| 5 | Atomically Flattening Technology at 850Â°C for Si(100) Surface. ECS Transactions, 2010, 28, 299-309. | 0.5 | 28 |
| 6 | Statistical analysis of Random Telegraph Noise reduction effect by separating channel from the interface. , 2012, , . | | 25 |
| 7 | A Statistical Evaluation of Random Telegraph Noise of In-Pixel Source Follower Equivalent Surface and Buried Channel Transistors. IEEE Transactions on Electron Devices, 2013, 60, 3555-3561. | 3.0 | 25 |
| 8 | Large-Scale Test Circuits for High-Speed and Highly Accurate Evaluation of Variability and Noise in Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistor Electrical Characteristics. Japanese Journal of Applied Physics, 2011, 50, 106701. | 1.5 | 21 |
| 9 | An Over 120 dB Single Exposure Wide Dynamic Range CMOS Image Sensor With Two-Stage Lateral Overflow Integration Capacitor. IEEE Transactions on Electron Devices, 2021, 68, 152-157. | 3.0 | 21 |
| 10 | [Paper] A Highly Ultraviolet Light Sensitive and Highly Robust Image Sensor Technology Based on Flattened Si Surface. ITE Transactions on Media Technology and Applications, 2014, 2, 123-130. | 0.5 | 20 |
| 11 | A High Near-Infrared Sensitivity Over 70-dB SNR CMOS Image Sensor With Lateral Overflow Integration Trench Capacitor. IEEE Transactions on Electron Devices, 2020, 67, 1653-1659. | 3.0 | 20 |
| 12 | Over 100 Million Frames per Second 368 Frames Global Shutter Burst CMOS Image Sensor with Pixel-wise Trench Capacitor Memory Array. Sensors, 2020, 20, 1086. | 3.8 | 19 |
| 13 | A global-shutter CMOS image sensor with readout speed of 1Tpixel/s burst and 780Mpixel/s continuous. , 2012, , . | | 16 |
| 14 | Analyzing correlation between multiple traps in RTN characteristics. , 2014, , . | | 15 |
| 15 | [Paper] A 20Mfps Global Shutter CMOS Image Sensor with Improved Light Sensitivity and Power Consumption Performances. ITE Transactions on Media Technology and Applications, 2016, 4, 149-154. | 0.5 | 15 |
| 16 | High performance and highly reliable novel CMOS devices using accumulation mode multi-gate and fully depleted SOI MOSFETs. Microelectronic Engineering, 2007, 84, 2105-2108. | 2.4 | 14 |
| 17 | Formation speed of atomically flat surface on Si (100) in ultra-pure argon. Microelectronic Engineering, 2011, 88, 3133-3139. | 2.4 | 14 |
| 18 | A dead-time free global shutter CMOS image sensor with in-pixel LOFIC and ADC using pixel-wis e connections. , 2016, , . | | 14 |

| # | ARTICLE | IF | CITATIONS |
|----|---|-----|-----------|
| 19 | The study of time constant analysis in random telegraph noise at the subthreshold voltage region. , 2013, , . | | 13 |
| 20 | Extraction of time constants ratio over nine orders of magnitude for understanding random telegraph noise in metal-oxide-semiconductor field-effect transistors. Japanese Journal of Applied Physics, 2014, 53, 04EC19. | 1.5 | 13 |
| 21 | Influence of silicon wafer surface roughness on semiconductor device characteristics. Japanese Journal of Applied Physics, 2020, 59, SMMB06. | 1.5 | 13 |
| 22 | HDR CMOS Image Sensors for Automotive Applications. IEEE Transactions on Electron Devices, 2022, 69, 2815-2823. | 3.0 | 13 |
| 23 | Photodiode dopant structure with atomically flat Si surface for high-sensitivity and stability to UV light. Proceedings of SPIE, 2012, , . | 0.8 | 12 |
| 24 | A linear response single exposure CMOS image sensor with 0.5e ^{&#x2212;} readout noise and 76ke ^{&#x2212;} full well capacity. , 2015, , . | | 12 |
| 25 | An over 1Mfps global shutter CMOS image sensor with 480 frame storage using vertical analog memory integration. , 2016, , . | | 12 |
| 26 | Low Leakage Current Al ₂ O ₃ Metal-Insulator-Metal Capacitors Formed By Atomic Layer Deposition at Optimized Process Temperature and O ₂ Post Deposition Annealing. ECS Transactions, 2016, 72, 91-100. | 0.5 | 12 |
| 27 | Random telegraph noise measurement and analysis based on arrayed test circuit toward high S/N CMOS image sensors. , 2016, , . | | 12 |
| 28 | An Optical Filter-Less CMOS Image Sensor with Differential Spectral Response Pixels for Simultaneous UV-Selective and Visible Imaging. Sensors, 2020, 20, 13. | 3.8 | 12 |
| 29 | A Highly Robust Silicon Ultraviolet Selective Radiation Sensor Using Differential Spectral Response Method. Sensors, 2019, 19, 2755. | 3.8 | 11 |
| 30 | A Global Shutter Wide Dynamic Range Soft X-Ray CMOS Image Sensor With Backside-Illuminated Pinned Photodiode, Two-Stage Lateral Overflow Integration Capacitor, and Voltage Domain Memory Bank. IEEE Transactions on Electron Devices, 2021, 68, 2056-2063. | 3.0 | 10 |
| 31 | Atomically flattening of Si surface of silicon on insulator and isolation-patterned wafers. Japanese Journal of Applied Physics, 2015, 54, 04DA04. | 1.5 | 9 |
| 32 | Three-Step Room-Temperature Cleaning of Bare Silicon Surface for Radical-Reaction-Based Semiconductor Manufacturing. Journal of the Electrochemical Society, 2009, 156, H10. | 2.9 | 8 |
| 33 | Evaluation for Anomalous Stress-Induced Leakage Current of Gate SiO_2 Films Using Array Test Pattern. IEEE Transactions on Electron Devices, 2011, 58, 3307-3313. | 3.0 | 8 |
| 34 | Visualization of Single Atomic Steps on An Ultra-Flat Si(100) Surface by Advanced Differential Interference Contrast Microscopy. Electrochemical and Solid-State Letters, 2011, 14, H351. | 2.2 | 8 |
| 35 | A CMOS image sensor with dual pixel reset voltage for high accuracy ultraviolet light absorption spectral imaging. Japanese Journal of Applied Physics, 2019, 58, SBBL03. | 1.5 | 8 |
| 36 | Hot Carrier Instability Mechanism in Accumulation-Mode Normally-off SOI nMOSFETs and Their Reliability Advantage. ECS Transactions, 2007, 6, 113-118. | 0.5 | 7 |

| # | ARTICLE | IF | CITATIONS |
|----|---|-----|-----------|
| 37 | Capacitance-Voltage Measurement Method for Ultrathin Gate Dielectrics Using LC Resonance Circuit. IEEE Transactions on Semiconductor Manufacturing, 2006, 19, 43-49. | 1.7 | 6 |
| 38 | Performance Comparison of Ultrathin Fully Depleted Silicon-on-Insulator Inversion-, Intrinsic-, and Accumulation-Mode Metal-Oxide-Semiconductor Field-Effect Transistors. Japanese Journal of Applied Physics, 2008, 47, 2668-2671. | 1.5 | 6 |
| 39 | Analysis of the Low-Frequency Noise Reduction in Si(100) Metal-Oxide-Semiconductor Field-Effect Transistors. Japanese Journal of Applied Physics, 2011, 50, 04DC01. | 1.5 | 6 |
| 40 | Gate SiO ₂ Film Integrity on Ultra-Pure Argon Anneal (100) Silicon Surface. ECS Transactions, 2011, 41, 147-156. | 0.5 | 6 |
| 41 | Demonstrating distribution of SILC values at individual leakage spots. , 2013, , . | | 6 |
| 42 | A UV Si-photodiode with almost 100% internal Q.E. and high transmittance on-chip multilayer dielectric stack. Proceedings of SPIE, 2013, , . | 0.8 | 6 |
| 43 | A Preliminary Chip Evaluation toward Over 50Mfps Burst Global Shutter Stacked CMOS Image Sensor. IS&T International Symposium on Electronic Imaging, 2018, 2018, 398-1-398-4. | 0.4 | 6 |
| 44 | Characterization for High-Performance CMOS Using In-Wafer Advanced Kelvin-Contact Device Structure. IEEE Transactions on Semiconductor Manufacturing, 2009, 22, 126-133. | 1.7 | 5 |
| 45 | Highly Reliable Radical SiO ₂ Films on Atomically Flat Silicon Surface Formed by Low Temperature Pure Ar Annealing. Japanese Journal of Applied Physics, 2011, 50, 10PB05. | 1.5 | 5 |
| 46 | Advanced Direct-Polishing Process Development of Non-Porous Ultralow-Dielectric Fluorocarbon with Plasma Treatment on Cu Interconnects. Journal of the Electrochemical Society, 2012, 159, H407-H411. | 2.9 | 5 |
| 47 | Cu Single Damascene Integration of an Organic Nonporous Ultralow-Dielectric Fluorocarbon Dielectric Deposited by Microwave-Excited Plasma-Enhanced CVD. IEEE Transactions on Electron Devices, 2012, 59, 1445-1453. | 3.0 | 5 |
| 48 | Analysis of pixel gain and linearity of CMOS image sensor using floating capacitor load readout operation. , 2015, , . | | 5 |
| 49 | Introduction of Atomically Flattening of Si Surface to Large-Scale Integration Process Employing Shallow Trench Isolation. ECS Journal of Solid State Science and Technology, 2016, 5, P67-P72. | 1.8 | 5 |
| 50 | [Papers] Statistical Analyses of Random Telegraph Noise in Pixel Source Follower with Various Gate Shapes in CMOS Image Sensor. ITE Transactions on Media Technology and Applications, 2018, 6, 163-170. | 0.5 | 5 |
| 51 | Impact of Channel Direction Dependent Low Field Hole Mobility on (100) Orientation Silicon Surface. Japanese Journal of Applied Physics, 2011, 50, 04DC03. | 1.5 | 5 |
| 52 | Examination of degradation mechanism due to negative bias temperature stress from a perspective of hole energy for accurate lifetime prediction. Microelectronics Reliability, 2007, 47, 409-418. | 1.7 | 4 |
| 53 | NBTI Mechanism Based on Hole-Injection for Accurate Lifetime Prediction. ECS Transactions, 2007, 6, 229-243. | 0.5 | 4 |
| 54 | Circuit level prediction of device performance degradation due to negative bias temperature stress. Microelectronics Reliability, 2007, 47, 930-936. | 1.7 | 4 |

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| 55 | Accurate negative bias temperature instability lifetime prediction based on hole injection. Microelectronics Reliability, 2008, 48, 1649-1654. | 1.7 | 4 |
| 56 | A pixel-shared CMOS image sensor using lateral overflow gate. , 2009, , . | | 4 |
| 57 | Data Analysis Technique of Atomic Force Microscopy for Atomically Flat Silicon Surfaces. IEICE Transactions on Electronics, 2009, E92-C, 664-670. | 0.6 | 4 |
| 58 | Ultra-low series resistance W/ErSi₂/n⁺-Si and W/Pd₂/Si_p-Si S/D electrodes for advanced CMOS platform. , 2010, , . | | 4 |
| 59 | A prototype high-speed CMOS image sensor with 10,000,000 fps burst-frame rate and 10,000 fps continuous-frame rate. Proceedings of SPIE, 2011, , . | 0.8 | 4 |
| 60 | Impact of Channel Direction Dependent Low Field Hole Mobility on (100) Orientation Silicon Surface. Japanese Journal of Applied Physics, 2011, 50, 04DC03. | 1.5 | 4 |
| 61 | Recovery Characteristics of Anomalous Stress-Induced Leakage Current of 5.6 nm Oxide Films. Japanese Journal of Applied Physics, 2012, 51, 04DC02. | 1.5 | 4 |
| 62 | Color reproductivity improvement with additional virtual color filters for WRGB image sensor. , 2013, , . | | 4 |
| 63 | A wide dynamic range CMOS image sensor with 200~1100 nm spectral sensitivity and high robustness to UV light exposure. Japanese Journal of Applied Physics, 2014, 53, 04EE07. | 1.5 | 4 |
| 64 | Low Temperature Atomically Flattening of Si Surface of Shallow Trench Isolation Pattern. ECS Transactions, 2015, 66, 285-292. | 0.5 | 4 |
| 65 | An ultraviolet radiation sensor using differential spectral response of silicon photodiodes. , 2015, , . | | 4 |
| 66 | [Paper] A CMOS Image Sensor with 240 μV Conversion Gain, 200 ke⁺ Full Well Capacity, 190-1000 nm Spectral Response and High Robustness to UV light. ITE Transactions on Media Technology and Applications, 2016, 4, 116-122. | 0.5 | 4 |
| 67 | [Paper] Analysis and Reduction Technologies of Floating Diffusion Capacitance in CMOS Image Sensor for Photon-Countable Sensitivity. ITE Transactions on Media Technology and Applications, 2016, 4, 91-98. | 0.5 | 4 |
| 68 | A high sensitivity 20Mfps CMOS image sensor with readout speed of 1Tpixel/sec for visualization of ultra-high speed phenomena. Proceedings of SPIE, 2017, , . | 0.8 | 4 |
| 69 | Hole-Trapping Process at Al ₂ O ₃ /GaN Interface Formed by Atomic Layer Deposition. IEEE Electron Device Letters, 2017, 38, 1309-1312. | 3.9 | 4 |
| 70 | A 24.3Me⁺ Full Well Capacity CMOS Image Sensor with Lateral Overflow Integration Trench Capacitor for High Precision Near Infrared Absorption Imaging. , 2018, , . | | 4 |
| 71 | Effect of drain current on appearance probability and amplitude of random telegraph noise in low-noise CMOS image sensors. Japanese Journal of Applied Physics, 2018, 57, 04FF08. | 1.5 | 4 |
| 72 | A High Sensitivity and Compact Real Time Gas Concentration Sensor for Semiconductor and Electronic Device Manufacturing Process. ECS Transactions, 2018, 85, 1399-1405. | 0.5 | 4 |

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|----|--|-----|-----------|
| 73 | [Papers] Impacts of Random Telegraph Noise with Various Time Constants and Number of States in Temporal Noise of CMOS Image Sensors. ITE Transactions on Media Technology and Applications, 2018, 6, 171-179. | 0.5 | 4 |
| 74 | A high-sensitivity compact gas concentration sensor using ultraviolet light absorption with a heating function for a high-precision trimethyl aluminum gas supply system. Japanese Journal of Applied Physics, 2019, 58, SBBL04. | 1.5 | 4 |
| 75 | Modification of copper and copper oxide surface states due to isopropyl alcohol treatment toward area-selective processes. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2021, 39, . | 2.1 | 4 |
| 76 | High capacitance density highly reliable textured deep trench SiN capacitors toward 3D integration. Japanese Journal of Applied Physics, 2021, 60, SBBC06. | 1.5 | 4 |
| 77 | A 2.8 Åµm Pixel-Pitch 55 ke ⁺ Full-Well Capacity Global-Shutter Complementary Metal Oxide Semiconductor Image Sensor Using Lateral Overflow Integration Capacitor. Japanese Journal of Applied Physics, 2013, 52, 04CE01. | 1.5 | 4 |
| 78 | Accurate Circuit Performance Prediction Model and Lifetime Prediction Method of NBT Stressed Devices for Highly Reliable ULSI Circuits. , 2006, , . | | 3 |
| 79 | A wide dynamic range checkered-color CMOS image sensor with IR-Cut RGB and visible-to-near-IR pixels. , 2009, , . | | 3 |
| 80 | Pixel Scaling in Complementary Metal Oxide Silicon Image Sensor with Lateral Overflow Integration Capacitor. Japanese Journal of Applied Physics, 2010, 49, 04DE03. | 1.5 | 3 |
| 81 | A test structure for statistical evaluation of pn junction leakage current based on CMOS image sensor technology. , 2010, , . | | 3 |
| 82 | Statistical evaluation of dynamic junction leakage current fluctuation using a simple arrayed capacitors circuit. , 2010, , . | | 3 |
| 83 | Electrical Properties of Silicon Nitride Using High Density and Low Plasma Damage PECVD Formed at 400ÅC. ECS Transactions, 2012, 45, 421-428. | 0.5 | 3 |
| 84 | A Test Circuit for Statistical Evaluation of \$p-n\$ Junction Leakage Current and its Noise. IEEE Transactions on Semiconductor Manufacturing, 2012, 25, 303-309. | 1.7 | 3 |
| 85 | A test circuit for extremely low gate leakage current measurement of 10 aA for 80,000 MOSFETs in 80 s. , 2012, , . | | 3 |
| 86 | A Test Circuit for Extremely Low Gate Leakage Current Measurement of 10 aA for 80 000 MOSFETs in 80 s. IEEE Transactions on Semiconductor Manufacturing, 2013, 26, 288-295. | 1.7 | 3 |
| 87 | High Selectivity in Dry Etching of Silicon Nitride over Si Using a Novel Hydrofluorocarbon Etch Gas in a Microwave Excited Plasma for FinFET. ECS Transactions, 2014, 61, 29-37. | 0.5 | 3 |
| 88 | Ultra-high speed video capturing of time dependent dielectric breakdown of metal-oxide-silicon capacitor up to 10M frame per second. Proceedings of SPIE, 2014, , . | 0.8 | 3 |
| 89 | Solid State Devices and Materials. Japanese Journal of Applied Physics, 2014, 53, 04E001. | 1.5 | 3 |
| 90 | A 1024Å—1 linear photodiode array sensor with fast readout speed flexible pixel-level integration time and high stability to UV light exposure. , 2014, , . | | 3 |

| # | ARTICLE | IF | CITATIONS |
|-----|---|-----|-----------|
| 91 | Carrier mobility characteristics of (100), (110), and (551) oriented atomically flattened Si surfaces for fin structure design of multi-gate metal-insulator-silicon field-effect transistors. Japanese Journal of Applied Physics, 2014, 53, 04EC04. | 1.5 | 3 |
| 92 | Pixel structure with 10 nsec fully charge transfer time for the 20m frame per second burst CMOS image sensor. Proceedings of SPIE, 2014, , . | 0.8 | 3 |
| 93 | [Paper] Floating Capacitor Load Readout Operation for Small, Low Power Consumption and High S/N Ratio CMOS Image Sensors. ITE Transactions on Media Technology and Applications, 2016, 4, 99-108. | 0.5 | 3 |
| 94 | Impact of SiO ₂ /Si interface micro-roughness on SILC distribution and dielectric breakdown: A comparative study with atomically flattened devices. , 2017, , . | | 3 |
| 95 | [Papers] A Multi Spectral Imaging System with a 71dB SNR 190-1100 nm CMOS Image Sensor and an Electrically Tunable Multi Bandpass Filter. ITE Transactions on Media Technology and Applications, 2018, 6, 187-194. | 0.5 | 3 |
| 96 | Resistance Measurement Platform for Statistical Analysis of Next Generation Memory Materials. , 2019, , . | | 3 |
| 97 | [Invite Paper] High Accuracy High Spatial Resolution and Real-Time CMOS Proximity Capacitance Image Sensor Technology and its Applications. ITE Transactions on Media Technology and Applications, 2021, 9, 122-127. | 0.5 | 3 |
| 98 | Over 100 million frames per second high speed global shutter CMOS image sensor. , 2019, , . | | 3 |
| 99 | Large-Scale Test Circuits for High-Speed and Highly Accurate Evaluation of Variability and Noise in Metal-Oxide-Semiconductor Field-Effect Transistor Electrical Characteristics. Japanese Journal of Applied Physics, 2011, 50, 106701. | 1.5 | 3 |
| 100 | On the Interface Flattening Effect and Gate Insulator Breakdown Characteristic of Radical Reaction Based Insulator Formation Technology. Japanese Journal of Applied Physics, 2012, 51, 02BA01. | 1.5 | 3 |
| 101 | Two High-Precision Proximity Capacitance CMOS Image Sensors with Large Format and High Resolution. Sensors, 2022, 22, 2770. | 3.8 | 3 |
| 102 | A 70-dB SNR High-Speed Global Shutter CMOS Image Sensor for <i>in Situ</i> Fluid Concentration Distribution Measurements. IEEE Transactions on Electron Devices, 2022, 69, 2965-2972. | 3.0 | 3 |
| 103 | Modeling and Implementation of Subthreshold Characteristics of Accumulation-Mode MOSFETs for Various SOI Layer Thickness and Impurity Concentrations. SOI Conference, Proceedings of the IEEE International, 2007, , . | 0.0 | 2 |
| 104 | Characterization of MOSFETs intrinsic performance using in-wafer advanced Kelvin-contact device structure for high performance CMOS LSIs. , 2008, , . | | 2 |
| 105 | Atomically flat gate insulator/silicon (100) interface formation introducing high mobility, ultra-low noise, and small characteristics variation CMOSFET. , 2008, , . | | 2 |
| 106 | Impact of Work Function Optimized S/D Silicide Contact for High Current Drivability CMOS. ECS Transactions, 2010, 28, 315-324. | 0.5 | 2 |
| 107 | A CMOS image sensor using floating capacitor load readout operation. Proceedings of SPIE, 2013, , . | 0.8 | 2 |
| 108 | A Column-Parallel Hybrid Analog-to-Digital Converter Using Successive-Approximation-Register and Single-Slope Architectures with Error Correction for Complementary Metal Oxide Silicon Image Sensors. Japanese Journal of Applied Physics, 2013, 52, 04CE04. | 1.5 | 2 |

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| 109 | A statistical evaluation of low frequency noise of in-pixel source follower-equivalent transistors with various channel types and body bias. Proceedings of SPIE, 2013, , . | 0.8 | 2 |
| 110 | A novel analysis of oxide breakdown based on dynamic observation using ultra-high speed video capturing up to 10,000,000 frames per second. , 2014, , . | | 2 |
| 111 | Si image sensors with wide spectral response and high robustness to ultraviolet light exposure. IEICE Electronics Express, 2014, 11, 20142004-20142004. | 0.8 | 2 |
| 112 | 190-1100 nm Waveband multispectral imaging system using high light resistance wide dynamic range CMOS image sensor. , 2016, , . | | 2 |
| 113 | A high sensitivity compact gas concentration sensor using UV light and charge amplifier circuit. , 2016, , . | | 2 |
| 114 | A CMOS Proximity Capacitance Image Sensor with $16\mu\text{m}$ Pixel Pitch, 0.1aF Detection Accuracy and 60 Frames Per Second. , 2018, , . | | 2 |
| 115 | Statistical Analysis of Threshold Voltage Variation Using MOSFETs With Asymmetric Source and Drain. IEEE Electron Device Letters, 2018, 39, 1836-1839. | 3.9 | 2 |
| 116 | Resistance Measurement Platform for Statistical Analysis of Emerging Memory Materials. IEEE Transactions on Semiconductor Manufacturing, 2020, 33, 232-239. | 1.7 | 2 |
| 117 | High reliability CoFeB/MgO/CoFeB magnetic tunnel junction fabrication using low-damage ion beam etching. Japanese Journal of Applied Physics, 2020, 59, SGGB05. | 1.5 | 2 |
| 118 | Highly Reliable Radical SiO ₂ Films on Atomically Flat Silicon Surface Formed by Low Temperature Pure Ar Annealing. Japanese Journal of Applied Physics, 2011, 50, 10PB05. | 1.5 | 2 |
| 119 | Recovery Characteristics of Anomalous Stress-Induced Leakage Current of 5.6 nm Oxide Films. Japanese Journal of Applied Physics, 2012, 51, 04DC02. | 1.5 | 2 |
| 120 | An Over 120dB Dynamic Range Linear Response Single Exposure CMOS Image Sensor with Two-stage Lateral Overflow Integration Trench Capacitors. IS&T International Symposium on Electronic Imaging, 2020, 32, 143-1-143-6. | 0.4 | 2 |
| 121 | Accurate circuit performance prediction model and lifetime prediction method of nbt stressed devices for highly reliable ulsi circuits. , 0, , . | | 1 |
| 122 | Three-Step Room Temperature Wet Cleaning Process for Silicon Substrate. Solid State Phenomena, 2009, 145-146, 189-192. | 0.3 | 1 |
| 123 | A Study on Very High Performance Novel Balanced Fully Depleted Silicon-on-Insulator Complementary Metal-Oxide Semiconductor Field-Effect Transistors on Si(110) Using Accumulation-Mode Device Structure for Radio-Frequency Analog Circuits. Japanese Journal of Applied Physics, 2009, 48, 04C047. | 1.5 | 1 |
| 124 | On the Interface Flattening Effect and Gate Insulator Breakdown Characteristic of Radical Reaction Based Insulator Formation Technology. Japanese Journal of Applied Physics, 2012, 51, 02BA01. | 1.5 | 1 |
| 125 | Integration Process Development for Improved Compatibility with Organic Non-Porous Ultralow- k Dielectric Fluorocarbon on Advanced Cu Interconnects. Japanese Journal of Applied Physics, 2012, 51, 05EC03. | 1.5 | 1 |
| 126 | A novel chemically, thermally and electrically robust Cu interconnect structure with an organic non-porous ultralow- k dielectric fluorocarbon ($k=2.2$). , 2012, , . | | 1 |

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|-----|--|-----|-----------|
| 127 | Stress induced leakage current generated by hot-hole injection. Microelectronic Engineering, 2013, 109, 298-301. | 2.4 | 1 |
| 128 | Demonstrating individual leakage path from random telegraph signal of stress induced leakage current. , 2014, , . | | 1 |
| 129 | High quantum efficiency 200–1000 nm spectral response photodiodes with on-chip multiple high transmittance optical layers. , 2014, , . | | 1 |
| 130 | Publisherâ€™s Note: â€œA wide dynamic range CMOS image sensor with 200â€“1100 nm spectral sensitivity and high robustness to UV light exposureâ€•. Japanese Journal of Applied Physics, 2014, 53, 069204. | 1.5 | 1 |
| 131 | A statistical evaluation of effective time constants of random telegraph noise with various operation timings of in-pixel source follower transistors. Proceedings of SPIE, 2014, , . | 0.8 | 1 |
| 132 | Effect of Process Temperature of Al2O3 Atomic Layer Deposition Using Accurate Process Gasses Supply System. ECS Transactions, 2015, 66, 305-314. | 0.5 | 1 |
| 133 | Analysis of breakdown voltage of area surrounded by multiple trench gaps in 4 kV monolithic isolator for communication network interface. Japanese Journal of Applied Physics, 2015, 54, 04DB01. | 1.5 | 1 |
| 134 | Measurement and Analysis of Seismic Response in Semiconductor Manufacturing Equipment. IEEE Transactions on Semiconductor Manufacturing, 2015, 28, 289-296. | 1.7 | 1 |
| 135 | Proposal of tunneling- and diffusion-current hybrid MOSFET: A device simulation study. Japanese Journal of Applied Physics, 2016, 55, 04ED12. | 1.5 | 1 |
| 136 | Evaluating Work-Function and Composition of ErSix on Various Surface Orientation of Silicon. ECS Journal of Solid State Science and Technology, 2016, 5, P608-P613. | 1.8 | 1 |
| 137 | Introduction of a High Selectivity Etching Process with Advanced SiNx Etch Gas in the Fabrication of FinFET Structures. ECS Transactions, 2016, 72, 23-30. | 0.5 | 1 |
| 138 | Cameras with On-chip Memory CMOS Image Sensors. , 2018, , 103-124. | | 1 |
| 139 | High Speed and Narrow-Bandpass Liquid Crystal Filter for Real-Time Multi Spectral Imaging Systems. IEICE Transactions on Electronics, 2018, E101.C, 897-900. | 0.6 | 1 |
| 140 | A high-precision 1 Î©â€“10 MÎ© range resistance measurement platform for statistical evaluation of emerging memory materials. Japanese Journal of Applied Physics, 2020, 59, SGGL03. | 1.5 | 1 |
| 141 | Science Based New Silicon Technologies Exhibiting Super High Performance due to Radical-reaction-based Semiconductor Manufacturing. Journal of the Korean Physical Society, 2011, 59, 391-401. | 0.7 | 1 |
| 142 | Integration Process Development for Improved Compatibility with Organic Non-Porous Ultralow- <i>k</i> /i> Dielectric Fluorocarbon on Advanced Cu Interconnects. Japanese Journal of Applied Physics, 2012, 51, 05EC03. | 1.5 | 1 |
| 143 | [Paper] A High Quantum Efficiency High Readout Speed 1024 Pixel Ultraviolet-Visible-Near Infrared Waveband Photodiode Array. ITE Transactions on Media Technology and Applications, 2016, 4, 109-115. | 0.5 | 1 |
| 144 | Accuracy and Applicability of Low-Frequency SCS â€“ VS Measurement Methods for Characterization of Ultrathin Gate Dielectrics With Large Current. IEEE Transactions on Electron Devices, 2007, 54, 1115-1124. | 3.0 | 0 |

| # | ARTICLE | IF | CITATIONS |
|-----|---|------|-----------|
| 145 | Different Types of Degradation and Recovery Mechanisms on NBT Stress for Thin SiO ₂ Films by On-The-Fly Measurement. ECS Transactions, 2009, 19, 339-350. | 0.5 | 0 |
| 146 | A robust color signal processing with wide dynamic range WRGB CMOS image sensor. Proceedings of SPIE, 2011, , . | 0.8 | 0 |
| 147 | Different Properties of Erbium Silicides on Si(100) and Si(551) Orientation Surfaces. ECS Transactions, 2011, 41, 365-373. | 0.5 | 0 |
| 148 | New analog readout architecture for low noise CMOS image sensors using column-parallel forward noise-canceling circuitry. Proceedings of SPIE, 2013, , . | 0.8 | 0 |
| 149 | A CMOS image sensor using column-parallel forward noise-canceling circuitry. Japanese Journal of Applied Physics, 2014, 53, 04EE14. | 1.5 | 0 |
| 150 | UV/VIS/NIR imaging technologies: challenges and opportunities. Proceedings of SPIE, 2015, , . | 0.8 | 0 |
| 151 | Image Electronics Information Sensing. Kyokai Joho Imeji Zasshi/Journal of the Institute of Image Information and Television Engineers, 2016, 70, 609-622. | 0.1 | 0 |
| 152 | Analysis and reduction of leakage current of 2 kV monolithic isolator with wide trench spiral isolation structure. Japanese Journal of Applied Physics, 2016, 55, 04EF07. | 1.5 | 0 |
| 153 | Formation technology of flat surface with epitaxial growth on ion-implanted (100)-oriented Si surface of thin silicon-on-insulator. Japanese Journal of Applied Physics, 2017, 56, 105503. | 1.5 | 0 |
| 154 | Atomically flat interface for noise reduction in SOI-MOSFETs. , 2017, , . | | 0 |
| 155 | High Sensitivity and High Readout Speed Electron Beam Detector using Steep pn Junction Si diode for Low Acceleration Voltage. IS&T International Symposium on Electronic Imaging, 2017, 29, 14-17. | 0.4 | 0 |
| 156 | Solid State Devices and Materials. Japanese Journal of Applied Physics, 2018, 57, 04F001. | 1.5 | 0 |
| 157 | Experimental investigation of localized stress-induced leakage current distribution in gate dielectrics using array test circuit. Japanese Journal of Applied Physics, 2018, 57, 04FE11. | 1.5 | 0 |
| 158 | Meeting matters. Nature Electronics, 2018, 1, 608-609. | 26.0 | 0 |
| 159 | Low-Temperature Deposition of Silicon Nitride Films Using Ultraviolet-Irradiated Ammonia. ECS Journal of Solid State Science and Technology, 2019, 8, P715-P718. | 1.8 | 0 |
| 160 | Impact on the Conductance Method of the Asymmetry in the AC Response Induced by Interface Trap Levels. ECS Journal of Solid State Science and Technology, 2021, 10, 043004. | 1.8 | 0 |
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